

Title (en)  
METHOD OF FABRICATING A GATE STACK AT LOW TEMPERATURE

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES MEHRSCHICHT-GATES BEI NIEDRIGER TEMPERATUR

Title (fr)  
PROCEDE D'EMPILEMENT DE GRILLE A BASSE TEMPERATURE

Publication  
**EP 1425785 A2 20040609 (EN)**

Application  
**EP 02798410 A 20020826**

Priority  

- US 0227230 W 20020826
- US 31656201 P 20010831

Abstract (en)  
[origin: TW559916B] The present invention relates to methods for forming dielectric layers on a substrate, such as in an integrated circuit. In one aspect of the invention, a thin interfacial layer is formed (30). The interfacial layer is preferably an oxide layer and a high-k material is preferably deposited on the interfacial layer by a process that does not cause substantial further growth of the interfacial layer. For example, water vapor may be used as an oxidant source during high-k deposition at less than or equal to about 300 DEG C.

IPC 1-7  
**H01L 21/28**

IPC 8 full level  
**H01L 21/28** (2006.01)

Citation (search report)  
See references of WO 03041124A2

DOCDB simple family (publication)  
EP 1425785 A2 20040609; TW 559916 B 20031101

DOCDB simple family (application)  
EP 02798410 A 20020826; TW 91119485 A 20020828